

Dynamic Differential Hall Effect Sensor

TLE4925/TLE4925C

Data Sheet Version 6.0

Features

- High sensitivity
- Single chip solution
- Symmetrical thresholds
- High resistance to Piezo effects
- South and north pole pre-induction possible
- Low cut-off frequency
- Digital output signal
- Advanced performance by dynamic self calibration principle
- Two-wire and three-wire configuration possible
- Wide operating temperature range
- Fast start-up time
- Large operating air-gaps
- Reverse voltage protection at Vs- PIN
- Short- circuit and over temperature protection of output
- Digital output signal (voltage interface)
- Module style package with two 4.7nF integrated capacitors (TLE4925C)

Туре	Marking	Ordering Code	Package	
TLE4925	25	Q62705-K677	PG-SSO-3-6	
TLE4925C	25C	Q62705-K676	PG-SSO-3-9	

General Information

The TLE4925/TLE4925C is an active Hall sensor suited to detect the motion and position of ferromagnetic and permanent magnet structures. An additional self-calibration module has been implemented to achieve optimum accuracy during normal running operation. It comes in a three-pin package for the supply voltage and an open drain output.





PG-SSO-3-9



Figure 1: Pin configuration	n in PG-SSO-3-6 and PG-SSO-3	;-9
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Pin	definition	and Function	
		••••••••••••	

Pin No.	Symbol	Function			
1	V _S	Supply Voltage			
2	GND	Ground			
3 Q		Open Drain Output			

Functional Description

The differential Hall sensor IC detects the motion and position of ferromagnetic and permanent magnet structures by measuring the differential flux density of the magnetic field. To detect ferromagnetic objects the magnetic field must be provided by a back biasing permanent magnet (south or north pole of the magnet attached to the rear unmarked side of the IC package).

Offset cancellation is achieved by advanced digital signal processing. Immediately after power-on motion is detected (start-up mode). After a few transitions the sensor has finished self-calibration and switches to a high-accuracy mode (running mode). In running mode switching occurs at signal zero-crossing of the arithmetic mean of max and min value of magnetic differential signal. ΔB is defined as difference between hall plate 1 and hall plate 2.





Figure 2: Block Diagram of TLE4925/TLE4925C

Circuit Description

The TLE4925/TLE4925C is comprised of a supply voltage regulator, a pair of hall probes, spaced at 2.5mm, differential amplifier, noise-shaping filter, comparator, advanced digital signal processor (DSP), A/D and D/A converter and an open drain output.

Startup mode:

The differential signal is digitized in the A/D converter and fed into the dsp part of the circuit. There a rising or falling transition is detected and the output stage is triggered accordingly. As the signal is not offset compensated at this time, the output does not necessarily switch at zero-crossing of the magnetic signal. Signal peaks are also detected in the digital circuit and their arithmetic mean value can be calculated. The offset of this mean value is determined and fed into the offset cancellation DAC. This procedure can be repeated with increasing accuracy. After few increments the IC is switched into the high accuracy running mode.



Running mode:

In running mode the output is triggered by the comparator. An offset cancellation feedback loop is formed by the A/D converter, dsp and offset cancellation D/A converter. In running mode switching always occurs at zero-crossing. It is only affected by the (small) remaining offset of the comparator and by the remaining propagation delay time of the signal path, mainly determined by the noise-shaping filter. Nevertheless signals below a defined threshold are not detected to avoid unwanted parasitic switching.



Figure 3: Startup of the device

At transition from startup-mode to running mode switching timing is moving from low-accuracy to high accuracy zero-crossing.



1.1 Absolute Maximum Ratings

No.	Parameter	Symbol	min	Тур	max	Unit	Remarks
1.1.1	Supply voltage	Vs	-18		18	V	-
			-24		24	V	1h with $R_{Series} \ge 200 \Omega^1$
			-26		26	V	5min with $R_{\text{Series}} \geq 200 \Omega^1$
			-28		28	V	1min with $R_{\text{Series}} \geq 200 \Omega^1$
1.1.2	Supply current	I _S	-10		25	mA	-
1.1.3	Output OFF voltage	V_{Q}	-0.3		18	V	-
			-0.3		24	V	1h with $R_{\text{Load}} \geq 500 \Omega$
			-0.3		26	V	5min with $R_{\text{Load}} \geq 500 \Omega$
			-1.0		-	V	1h (protected by internal
							series resistor)
1.1.4	Output ON voltage	V_{Q}	-		16	V	Current internal limited by
							short circuit protection
							(72h @ T _A < 40°C).
			-		18	V	Current internal limited by
							short circuit protection
							(1h @ T _A < 40°C).
			-		24	V	Current internal limited by
							short circuit protection
							(1min @ T _A < 40°C).
1.1.5	Continuous output	Ι _Q	-50		50	mA	-
110			10			*0	
1.1.6		lj	-40		455	°C	-
					155	۰ د	2000h (not additive)
					100	ں °C	1000h (not additive)
					105	ں د	3 x1 h (additive to the
					195	C	other life times)
1 1 7	Storago tomporaturo	т	40		150	°C	
1.1.7			-40		100		-
0.1.8	i nermai resistance	K _{th JA}			190	r./VV	Lower values are possible
	junction-air for						with overmoulded
	PG-SSO-3-6						devices.
	PG-SSO-3-9						
L							

Note: Stresses above those listed here may cause permanent damage to the device. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

¹ Accumulated life time.



1.2 ESD Protection

No.	Parameter	Symbol	max	Unit	Remarks
1.2.1	ESD – protection PG-SSO-3-9 PG-SSO-3-6	V_{ESD}	± 6 ± 4	kV kV	According to standard EIA/JESD22-A114-B Human Body Model (HBM 1500 Ohm/100pF)

2.1 Operating Range

No.	Parameter	Symbol	min	typ	max	Unit	Remarks
2.1.1	Supply voltage	Vs	3.3		18	V	Continuous
					24	V	1h with $R_{Series} \ge 200\Omega$
					26	V	5min with $R_{Series} \ge$ 200 Ω . Extended limits for parameters in characteristics.
			3			V	During test pulse 4. Limited performance possible
2.1.2	Supply voltage ripple	V_{SAC}			6	V_{pp}	V _S =13V; 0 < f < 50kHz
2.1.3	Continuous output OFF	V _Q	-0.3		18	V	Continuous
	voltage		-18		24	V	1h with $R_{\text{Load}} \geq 500 \Omega$
2.1.4	Continuous output ON current	Ι _Q	0		20	mA	V _{Qmax} =0.6V
2.1.5	Power on time	t _{on}			1	ms	Time to achieve specified accuracy After power on the output of the IC is always in high-state. After internal resets output is locked ² .

² Output of the IC is locked in present state (high-state or low-state) after an internal reset is launched. This reset happens typically every 780ms when there is no significant signal change. See also 2.2.14. A voltage reset causes a release of the output and output is in high state after power on again.



2.1.6	Operating junction	Tj	-40		°C	-
	temperature			155	°C	2000 h (not additive)
				165	°C	1000 h (not additive)
				175	Ŷ	168 h (not additive) reduced signal quality permittable (e.g. jitter)

Note: Unless otherwise noted, all temperatures refer to junction temperature.

For the supply voltage lower than 28V ($R_{Series} \ge 200\Omega$) and junction temperature lower than 195°C the magnetic and AC/DC characteristics can exceed the specification limits.

2.2 AC/DC Characteristics

Over operating range, unless otherwise specified. Typical values correspond to $V_{\rm S}\text{=}12V$ and $T_{A}\text{=}25^{\circ}\text{C}$

No.	Parameter	Symbol	min	typ	max	Unit	Remarks
2.2.1	Supply current	I _S	3	6.8	9	mA	-
2.2.2	Supply current @ 3.3V	I _{SVmin}	3	6.7	8	mA	V _S =3.3V
2.2.3	Supply current @ 24V	I _{Smax}	3	7	9.5	mA	V _S =24V
							$R_{Series} \geq 200 \Omega$
2.2.4	Output saturation voltage	V_{Qsat}		0.25	0.6	V	I _Q = 20mA
2.2.5	Output leakage current	I _{Qleak}		0.1	10	μA	V _Q = 18V
2.2.6	Current limit for short- Circuit protection	I _{Qshort}	30	60	80	mA	-
2.2.7	Junction temperature limit for output protection	T _{prot}	195	210	230	°C	-
2.2.8	Output rise time TLE4925C (PG-SSO-3-9)	t _r ³	4	12	20	μs	V_{Load} = 4.5 to 24V R _{Load} = 1.2k Ω ; C _{Load} = 4.7nF included
	TLE4925 (PG-SSO-3-6)		4	12	20	μs	in package. V_{Load} = 4.5 to 24V R_{Load} = 1.2k Ω ; C_{Load} = 4.7nF external capacitor.

³ value of capacitor: 4.7nF±10%; (excluded drift due to temperature); ceramic: X7R; maximum voltage: 100V. The rise time is defined as the time between the 10 and 90% value.



2.2.9	Output fall time	t _f ⁴					
	TLE4925C		0.5	0.9	1.3	μs	V _{Load} = 5V
	(PG-SSO-3-9)		0.65	1.15	1.65	μs	V _{Load} = 12V
							R_{Load} = 1.2k Ω ;
							C_{Load} = 4.7nF included
							in package.
			0.5	0.9	1.3	μs	$V_{Load} = 5V$
	ILE4925 (PG-SSO-3-6)		0.65	1.15	1.65	μs	V _{Load} = 12V
	(1 9-330-3-0)						$R_{Load} = 1.2 k\Omega;$
							$C_{Load} = 4.7 nF$
							external capacitor.
2.2.10	delay time	t _d	7	12.5	18	μs	Only valid for Tj=25°C.
	Falling edge				20 ⁵	μs	Tj=-40°C -Tj=175°C
	Rising edge				25 ⁶		Tj=-40°C -Tj=175°C
							Higher magnetic
							slopes and overshoots
							reduce t_d , because the
							signal is filtered
							internal.'
2.2.11	Temperature drift of	Δt_{d}	-6	3 ⁸	6	μs	Time over specified
	delay time of output to						temperature range;
	magnetic edge						not additional to t _d
2.2.12	Frequency range	f	0.001		8	kHz	Operation below 1Hz ⁹
2.2.13	Oscillator frequency	f _{OSC}	1.08	1.34	1.68	MHz	-
2.2.14	Offset recalibration time	t _{reset}	625	780	970	ms	Output locked to state
	after last output change						before recalibration
2.2.15	Clamping voltage	V _{Sclamp}	24	27.5		V	I _S = 20mA < 5min.
	V _s -Pin						
2.2.16	Clamping voltage Q- Pin	V_{Qclamp}	24	27.5		V	I _Q = 20mA < 5min.
2.2.17	Analog reset voltage	V _{sReset}		2.35	2.9	V	-

Note: The listed AC/DC and magnetic characteristics are ensured over the operating range of the integrated circuit. Typical characteristics specify mean values expected over the production spread. If not other specified, typical characteristics apply at $T_j = 25$ °C and V_S = 12 V.

⁴ see footnote 3.

 ⁵ only valid for the falling edge.
 ⁶ Not subject to production test-verified by design/characterisation
 ⁷ measured with a sinusoidal-field with 10mTpp and a frequency of 1kHz.

⁸ related to Tj= 175°C. ⁹ output will switch if magnetic signal is changing more that $2x |\Delta B_{min}|$ within offset recalibration time even below 1Hz once per magnetic edge, increased phase error is possible



2.3 Magnetic Characteristics in Running Mode

No.	Parameter	Symbol	min	typ	max	Unit	Remarks
2.3.1	Bias preinduction	B ₀	-500		500	mT	-
2.3.2	Differential bias induction	ΔB_0	-30		30	mT	-
2.3.3	Minimum signal amplitude	$ \Delta B_{min} $	0.55		1.5	mT	
2.3.4	Maximum signal amplitude	$ \Delta B_{max} $			100	mT	Additional to B ₀ ¹⁰
2.3.5	Resistivity against mechanical stress (piezo)	$ \Delta B_{min} $	-0.2		0.2	mT	F= 2N

Note: The listed characteristics are ensured over the operating range of the integrated circuit. Typical characteristics specify mean values expected over the production spread. If not otherwise specified, typical characteristics apply at $T_i=25^{\circ}C$ and the given supply voltage.

3.1 Self-calibration Characteristics

No.	Parameter	Symbol	min	typ	max	Unit	Remarks
3.1.1	No. of magnetic edges for first output switching	n _{Start}			2	-	latest 2 nd magnetic edge will cause output switching
3.1.2	No. of magnetic edges to enter calibrated mode	n _{Calib}			6	-	Low phase accuracy permitted. See 3.1.7 7 th edge with high accuracy. Valid for sinusoidal signal without noise influence
3.1.3	Duty cycle in running mode ¹¹	Dty	45	50	55	%	∆B _{PP} = 10mT ideal sinusoidal input signal (Tj=25°C)
			40	50	60	%	ΔB_{PP} = 10mT ideal sinusoidal input signal (-40°C $\leq T_j < 175$ °C)
3.1.4	Signal jitter in running mode; 1 sigma value ⁵	σ1		$\leq \pm 0.11^{12}$		%	∆B _{PP} = 10mT ideal sinusoidal input signal; T _j <150°C

¹⁰ exceeding this limit might result in decreased duty cycle performance. With higher values the internal measured signal will be clipped. This will decrease the phase accuracy.

¹¹ this corresponds to a $\Delta B_0 = 0$ mT (magnetic offset). ¹² depends largely on $|\Delta B_{min}|$ magnetic signal steepness and also on frequency.



3.1.5	Signal Jitter in running	σ2 σ3		≤ ±0.16 ≤ ±0.11		%	ΔB_{PP} = 10mT ideal sinusoidal input signal; 150°C \leq T _j < 175°C ΔB_{PP} = 10mT ideal
	mode at power supply of Vs=13V and ripple ±3V; 1 sigma value*						sinusoidal input signal; T _j <150°C
3.1.6	Effective noise value of the magnetic switching points, 1 sigma value	B _{neff}		25		μТ	$T_j = 25$ °C; The magnetic noise is normal distributed, nearly independent to frequency and without sampling noise or digital noise effects. The typical value represents the rms- value here and corresponds therefore to 1 σ probability of normal distribution. Consequently a 3 σ value corresponds to 0.3% probability of appearance.
					70	μT	The max value corresponds to the rms-values in the full temperature range and includes technological spreads.
3.1.7	Uncalibrated phase error Magnetic edge 1-2 After 3 rd edge Magnetic edge 1-3				≤ ±90 ≤ ±55 ≤ ±90	0	Related to calibrated switching behaviour. ΔB_{PP} = 10mT ideal sinusoidal input signal ¹³ Magnetic fields close to 2x $ \Delta B_{min} $
3.1.8	Frequency distribution of signal jitter		Jitter li	shall be dist ke white noi	ributed se		-

¹³ smaller phase errors are possible at higher signal amplitudes, because sinus signal changes to a more rectangle signal.







$$\sigma 1...\sigma 3 = \frac{1}{T} \cdot \sqrt{\frac{1}{(n-1)} \cdot \sum (\Delta T)^2}$$

measurement condition: $n \ge 1000$

Figure 5 Definition of signal jitter



Application Configurations

Two possible applications are shown in **Figure 6** and **Figure 7** (Toothed and Magnet Wheel).

The difference between two-wire and three-wire application is shown in **Figure 10** for the TLE4925C and in **Figure 11** for the TLE4925.

Gear Tooth Sensing

In the case of ferromagnetic toothed wheel application the IC has to be biased by the south or north pole of a permanent magnet (e.g. $SmCO_5$ (Vacuumschmelze VX145)) with the dimensions 8 mm × 5 mm × 3 mm) which should cover both Hall probes.

The maximum air gap depends on

- the magnetic field strength (magnet used; pre-induction) and
- the toothed wheel that is used (dimensions, material, etc.; resulting differential field).









Figure 9

Signal Processing

Circuitry

TLE4925/TLE4925C, with Magnet Wheel

AEA01262





Figure 10 Application Circuits TLE4925C (capacitors added in package)





Figure 11 Application Circuits TLE4925 (capacitors to be added externally)





Figure 12 System Operation with hidden hysteresis



Appendix: Calculation of mechanical errors:



Systematic Phase Error ϕ

The systematic error comes in because of the delay-time between the threshold point and the time when the output is switching. It can be calculated as follows:

$$\varphi = \frac{360^\circ \bullet n}{60} \bullet t_d$$

- ϕ ... systematic phase error in °
- n ... speed of the camshaft-wheel in min⁻¹
- t_d ... delay time (see specification) in sec



Systematic Phase Error $\Delta \phi$

The systematic phase error includes the error due to the variation of the delay time with temperature and the error caused by the resolution of the threshold. It can be calculated in the following way:

$$\Delta \varphi_d = \frac{360^\circ \bullet n}{60} \bullet \Delta t_d$$

- $\Delta\phi_{d}$ ~ ... systematic phase error due to the variation of the delay time over temperature in $^{\circ}$
- n ... speed of the camshaft wheel in *min*⁻¹
- Δt_d ... variation of delay time over temperature in sec



Jitter (Repeatability)

The phase jitter is normally caused by the analogue system noise. If there is an update of the offset-DAC due to the algorithm, what could happen after each tooth, then an additional step in the phase occurs (see description of the algorithm). This is not included in the following calculations. The noise is transformed through the slope of the magnetic edge into a phase error. The phase jitter is determined by the two formulas:

$$\varphi_{Jitter_typ} = \frac{\partial \varphi}{\partial B} \bullet \left(B_{neff_typ} \right)$$

$$\varphi_{Jitter_max} = \frac{\partial \varphi}{\partial B} \bullet \left(B_{neff_max} \right)$$



ΦJitter_typ	 typical phase jitter at Tj=25°C in ° (1Sigma)
ϕ_{Jitter_max}	 maximum phase jitter at Tj=175°C in ° (3Sigma)
$\frac{\partial \varphi}{\partial B}$	 inverse of the magnetic slope of the edge in $^{\circ}/T$
B _{neff_typ}	 typical value of B_{diff} in T (1 σ -value at Tj=25°C)
B_{neff}_max	 maximum value of B_{diff} in T (3 σ -value at Tj=175°C)

Example:

Assumption:	n = 4500 min ⁻¹
	t _d = 14 μs
	$\Delta t_d = \pm 3 \ \mu s$
	$\frac{\partial B}{\partial B} = 3 \text{ mT/}^{\circ}$
	$\partial arphi$
	$B_{neff_{typ}} = \pm 40 \ \mu T$ (1 σ -value at Tj=25°C)
	$B_{neff_{max}} = \pm 210 \ \mu T$ (3 σ -value at Tj=175°C)

Calculation:	φ = 0.378°	 systematic phase error
	$\Delta \phi_d = \pm 0.081^\circ$	 systematic phase error due to delay time
variation		
	$\varphi_{\text{Jitter_typ}} = \pm 0.013^{\circ}$	 typical phase jitter (1σ-value at Tj=25°C)
	$\phi_{\text{Jitter_max}} = \pm 0.07^{\circ}$	 maximum phase jitter (3σ-value at Tj=175°C)



4.1 Electro Magnetic Compatibility - (values depend on R_{Series}!)

Ref. ISO 7637-1; see test circuit of figure 4 and 5;

No.	Parameter	Symbol	Level/typ	Status
4.1.1	Testpulse 1	V _{EMC}	IV / -100V	С
	Testpulse 2		IV / 100V	С
	Testpulse 3a		IV / -150V	A
	Testpulse 3b		IV / 100V	A
	Testpulse 4		IV / -7V	A
	Testpulse 5		IV / 86.5V	С

 $\Delta B_{PP} = 10mT \text{ (ideal sinusoidal signal); } V_{S} = 13.5V \pm 0.5V, \text{ } f_{B} = 1000Hz; \text{ } T = 25^{\circ}\text{C}; \text{ } R_{Series} \geq 200\Omega; \text{ } R_{S} \geq 200\Omega; \text{ }$

Note: Test criteria for status A: No missing pulse no additional pulse on the IC output signal plus duty cycle and jitter are in the specification limits.
 Test criteria for status B: No missing pulse no additional pulse on the IC output signal. (Output signal "OFF" means switching to the voltage of the pull-up resistor).
 Test criteria for status C: One or more parameter can be out of specification during the exposure but returns automatically to normal operation after exposure is removed.
 Test criteria for status E: IC destroyed.

Ref. ISO 7637-3; TP 1 and TP 2 ref. DIN 40839-3; see test circuit of figure 4 and 5;

ΔB_{PP} = 10mT (ideal sinus	oidal signal); V _S =13.5V ±	= 0.5V, f _B = 1000Hz; T	= $25^{\circ}C$; $R_{Series} \ge 200\Omega$;
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No.	Parameter	Symbol	Level/typ	Status
4.1.2	Testpulse 1 Testpulse 2	V _{EMC}	IV / -30V IV / 30V	A A
	Testpulse 3a		IV / -60V	A
	l estpulse 3b		IV / 40V	A

Ref. ISO 11452-3; see test circuit of figure 4 and 5; measured in TEM-cell;

$\Delta B_{PP} = 4mT$	(ideal sinusoidal s	ignal); V_{S} =13.5V ± 0,5V,	, f _B = 200Hz; T= 25°C; R	$_{\text{Series}} \ge 200\Omega;$

No.	Parameter	Symbol	Level/max	Remarks
4.1.3	EMC field strength	E _{TEM-Cell}	IV / 200V/m	AM=80%, f=1kHz;

Note: Stresses above those listed here may cause permanent damage to the device. Exposure to absolute maximum rating conditions for extended periods may affect device reliability. Test condition for the trigger window: $f_{B-field}=200$ Hz, $B_{pp}=4$ mT, vertical limits are ± 200 mV and horizontal limits are ± 200 µs.





Figure 13: Test Circuit for EMC tests (TLE4925C) – PG-SSO-3-9 Package



Figure 14: Test Circuit for EMC tests (TLE4925) – PG-SSO-3-6 Package







 Figure 15
 Package Dimensions (PG-SSO-3-9)





Figure 16 Hall probe spacing in the PG-SSO-3-9 package





Figure 17 Tape Loading Orientation in the PG-SSO-3-9 package





Figure 18 Package Dimensions (PG-SSO-3-6)







Figure 20 Tape Loading Orientation in the PG-SSO-3-6 package



Appendix A: Marking & data matrix code information:

Product is RoHS (restriction of hazardous substances) compliant when marked with letter "G" in front or after the date code marking.

As mentioned in information note N° **136/03** a data matrix code with 8x18 fields according to the ECC200 standard may be used for sensor production. Furthermore the marking technique on the front side of the device may be changed from a mask to a laser writing equipment. The information content (date code and device type) will hereby not be changed.

Please refer to your key account team or regional sales responsible if you need further information.

Example for data matrix code (rear side of sensor):



Comparison between mask writing vs. new laser writing:





Revision	History: February 200)5	Version 6.0
Previous Version: 5.0			
Page	Subjects (major changes since last	revision)	
6	ESD-protection max. value changed from 8 to 6kV		
24	Update package drawing: parallelisr	n	
27	Update comparison mask writing/las	ser writing	

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